Seong Keun Kim

List of Publications by Year
in descending order

159 papers	5,220 citations	76196 40 h-index	102304 66 g-index
159 all docs	159 docs citations	159 times ranked	6076 citing authors

#	Article	IF	Citations
1	Effects of oxygen sources on properties of atomic-layer-deposited ferroelectric hafnium zirconium oxide thin films. Ceramics International, 2022, 48, 3280-3286.	2.3	2
2	Cross-linked structure of self-aligned p-type SnS nanoplates for highly sensitive NO₂ detection at room temperature. Journal of Materials Chemistry A, 2022, 10, 4711-4719.	5.2	14
3	Atomically thin indium oxide transistors. Nature Electronics, 2022, 5, 129-130.	13.1	3
4	Stepwise growth of crystalline MoS₂ in atomic layer deposition. Journal of Materials Chemistry C, 2022, 10, 7031-7038.	2.7	5
5	Oxidation of thermoelectric Bi2Te3-based alloys by atomic layer deposition of Ru metal. Materials Letters, 2022, 320, 132321.	1.3	2
6	Thermal stress-assisted annealing to improve the crystalline quality of an epitaxial YSZ buffer layer on Si. Journal of Materials Chemistry C, 2022, 10, 10027-10036.	2.7	5
7	Enhancement of electrical performance of atomic layer deposited SnO films via substrate surface engineering. Journal of Materials Chemistry C, 2021, 9, 12314-12321.	2.7	6
8	Atomic-layer deposition of TiO2 thin films with a thermally stable (CpMe5)Ti(OMe)3 precursor. Applied Surface Science, 2021, 550, 149381.	3.1	14
9	Hot rolling process for texture development and grain refinement of n-type Bi2Te3 alloys. Materials Letters, 2021, 301, 130278.	1.3	2
10	Defect-Controlled, Scalable Layer-by-Layer Assembly of High-k Perovskite Oxide Nanosheets for All Two-Dimensional Nanoelectronics. Chemistry of Materials, 2021, 33, 8685-8692.	3.2	8
11	Atomic engineering of metastable BeO6 octahedra in a rocksalt framework. Applied Surface Science, 2020, 501, 144280.	3.1	8
12	Wafer-Scale, Conformal, and Low-Temperature Synthesis of Layered Tin Disulfides for Emerging Nonplanar and Flexible Electronics. ACS Applied Materials & Interfaces, 2020, 12, 2679-2686.	4.0	20
13	Investigation of phases and chemical states of tin titanate films grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 012404.	0.9	3
14	Substrate Surface Modification for Enlarging Two-Dimensional SnS Grains at Low Temperatures. Chemistry of Materials, 2020, 32, 9026-9033.	3.2	9
15	Highly sensitive flexible NO₂ sensor composed of vertically aligned 2D SnS₂ operating at room temperature. Journal of Materials Chemistry C, 2020, 8, 11874-11881.	2.7	38
16	Smart forensic kit: Real-time estimation of postmortem interval using a highly sensitive gas sensor for microbial forensics. Sensors and Actuators B: Chemical, 2020, 322, 128612.	4.0	0
17	Domain engineering of epitaxial (001) Bi2Te3 thin films by miscut GaAs substrate. Acta Materialia, 2020, 197, 309-315.	3.8	6
18	Combined hot extrusion and spark plasma sintering method for producing highly textured thermoelectric Bi2Te3 alloys. Journal of the European Ceramic Society, 2020, 40, 3042-3048.	2.8	11

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19	Carrier Modulation in Bi2Te3-Based Alloys via Interfacial Doping with Atomic Layer Deposition. Coatings, 2020, 10, 572.	1.2	10
20	Mapping thermoelectric properties of polycrystalline n-type Bi2Te3-xSex alloys by composition and doping level. Journal of Alloys and Compounds, 2020, 844, 155828.	2.8	7
21	Cation-Regulated Transformation for Continuous Two-Dimensional Tin Monosulfide. Chemistry of Materials, 2020, 32, 2313-2320.	3.2	21
22	3D architectures of single-crystalline complex oxides. Materials Horizons, 2020, 7, 1552-1557.	6.4	9
23	Enhanced thermal stability of Bi2Te3-based alloys via interface engineering with atomic layer deposition. Journal of the European Ceramic Society, 2020, 40, 3592-3599.	2.8	11
24	Atomic layer deposition of SnO2 thin films using tetraethyltin and H2O2. Ceramics International, 2019, 45, 20600-20605.	2.3	17
25	Crystal properties of atomic-layer deposited beryllium oxide on crystal and amorphous substrates. Semiconductor Science and Technology, 2019, 34, 115021.	1.0	4
26	Atomic layer deposition of Ta-doped SnO2 films with enhanced dopant distribution for thermally stable capacitor electrode applications. Applied Surface Science, 2019, 497, 143804.	3.1	11
27	Confined polaronic transport in (LaFeO3)n/(SrFeO3)1 superlattices. APL Materials, 2019, 7, .	2.2	5
28	Precision Interface Engineering of an Atomic Layer in Bulk Bi₂Te₃ Alloys for High Thermoelectric Performance. ACS Nano, 2019, 13, 7146-7154.	7.3	66
29	High-Performance Thin-Film Transistors of Quaternary Indiumâ€“Zincâ€“Tin Oxide Films Grown by Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2019, 11, 14892-14901.	4.0	48
30	Strategic Selection of the Oxygen Source for Low Temperatureâ€Atomic Layer Deposition of Al₂O₃ Thin Film. Advanced Electronic Materials, 2019, 5, 1800680.	2.6	13
31	Domain epitaxy of crystalline BeO films on GaN and ZnO substrates. Journal of the American Ceramic Society, 2019, 102, 3745-3752.	1.9	12
32	Impurity-free, mechanical doping for the reproducible fabrication of the reliable n-type Bi2Te3-based thermoelectric alloys. Acta Materialia, 2018, 150, 153-160.	3.8	23
33	Resistive Switching of Ta2O5-Based Self-Rectifying Vertical-Type Resistive Switching Memory. Journal of Electronic Materials, 2018, 47, 162-166.	1.0	7
34	MoO₂ as a thermally stable oxide electrode for dynamic random-access memory capacitors. Journal of Materials Chemistry C, 2018, 6, 13250-13256.	2.7	18
35	A novel class of oxynitrides stabilized by nitrogen dimer formation. Scientific Reports, 2018, 8, 14471.	1.6	6
36	A Ruâ€“Pt alloy electrode to suppress leakage currents of dynamic random-access memory capacitors. Nanotechnology, 2018, 29, 455202.	1.3	4

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37	Engineering of AlON interlayer in Al 2 O 3 /AlON/In 0.53 Ga 0.47 As gate stacks by thermal atomic layer deposition. Current Applied Physics, 2018, 18, 919-923.	1.1	0
38	Future of dynamic random-access memory as main memory. MRS Bulletin, 2018, 43, 334-339.	1.7	88
39	Laser-irradiated inclined metal nanocolumns for selective, scalable, and room-temperature synthesis of plasmonic isotropic nanospheres. Journal of Materials Chemistry C, 2018, 6, 6038-6045.	2.7	37
40	Low-temperature wafer-scale synthesis of two-dimensional SnS₂. Nanoscale, 2018, 10, 17712-17721.	2.8	30
41	Texture-induced reduction in electrical resistivity of p-type (Bi,Sb)2Te3 by a hot extrusion. Journal of Alloys and Compounds, 2018, 764, 261-266.	2.8	12
42	Interface Engineering for Extremely Large Grains in Explosively Crystallized TiO₂ Films Grown by Low-Temperature Atomic Layer Deposition. Chemistry of Materials, 2017, 29, 2046-2054.	3.2	19
43	Bio-fabrication of nanomesh channels of single-walled carbon nanotubes for locally gated field-effect transistors. Nanotechnology, 2017, 28, 025304.	1.3	4
44	Fabrication of high-performance p-type thin film transistors using atomic-layer-deposited SnO films. Journal of Materials Chemistry C, 2017, 5, 3139-3145.	2.7	81
45	Design and Experimental Investigation of Thermoelectric Generators for Wearable Applications. Advanced Materials Technologies, 2017, 2, 1600292.	3.0	28
46	Ta-Doped SnO₂ as a reductionâ€“resistant oxide electrode for DRAM capacitors. Journal of Materials Chemistry C, 2017, 5, 9405-9411.	2.7	19
47	A two-step synthesis process of thermoelectric alloys for the separate control of carrier density and mobility. Journal of Alloys and Compounds, 2017, 727, 191-195.	2.8	6
48	Synthesis of SnS Thin Films by Atomic Layer Deposition at Low Temperatures. Chemistry of Materials, 2017, 29, 8100-8110.	3.2	68
49	Suppression of bulk conductivity and large phase relaxation length in topological insulator Bi2-ÎˇSnÎ˙Te3 epitaxial thin films grown by Metal-Organic Chemical Vapor Deposition (MOCVD). Journal of Alloys and Compounds, 2017, 723, 942-947.	2.8	5
50	Growth and Characterization of BeO Thin Films Grown by Atomic Layer Deposition Using H₂O and O₃ as Oxygen Sources. Journal of Physical Chemistry C, 2017, 121, 17498-17504.	1.5	13
51	Atomic-Layer Deposition of Single-Crystalline BeO Epitaxially Grown on GaN Substrates. ACS Applied Materials & Interfaces, 2017, 9, 41973-41979.	4.0	14
52	Advanced Silicon-on-Insulator: Crystalline Silicon on Atomic Layer Deposited Beryllium Oxide. Scientific Reports, 2017, 7, 13205.	1.6	10
53	Triboelectric charge generation by semiconducting SnO2 film grown by atomic layer deposition. Electronic Materials Letters, 2017, 13, 318-323.	1.0	6
54	Wall-thickness-dependent strength of nanotubular ZnO. Scientific Reports, 2017, 7, 4327.	1.6	6

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55	Leaky Integrate-and-Fire Neuron Circuit Based on Floating-Gate Integrator. Frontiers in Neuroscience, 2016, 10, 212.	1.4	55
56	Harman Measurements for Thermoelectric Materials and Modules under Non-Adiabatic Conditions. Scientific Reports, 2016, 6, 39131.	1.6	19
57	Effect of spark plasma sintering conditions on the thermoelectric properties of (Bi0.25Sb0.75)2Te3 alloys. Journal of Alloys and Compounds, 2016, 678, 396-402.	2.8	25
58	Polarity-tunable spin transport in all-oxide multiferroic tunnel junctions. Nanoscale, 2016, 8, 10799-10805.	2.8	9
59	Wafer-scale growth of MoS₂thin films by atomic layer deposition. Nanoscale, 2016, 8, 10792-10798.	2.8	139
60	Correction of the Electrical and Thermal Extrinsic Effects in Thermoelectric Measurements by the Harman Method. Scientific Reports, 2016, 6, 26507.	1.6	11
61	Enhancement of Mechanical Hardness in SnO_xN_y with a Dense High-Pressure Cubic Phase of SnO₂. Chemistry of Materials, 2016, 28, 7051-7057.	3.2	23
62	Towards spin-polarized two-dimensional electron gas at a surface of an antiferromagnetic insulating oxide. Physical Review B, 2016, 94, .	1.1	6
63	Interfacial control of oxygen vacancy doping and electrical conduction in thin film oxide heterostructures. Nature Communications, 2016, 7, 11892.	5.8	77
64	Free-electron creation at the 60Â° twin boundary in Bi2Te3. Nature Communications, 2016, 7, 12449.	5.8	59
65	Correct extraction of frequency dispersion in accumulation capacitance in InGaAs metal-insulator-semiconductor devices. Electronic Materials Letters, 2016, 12, 768-772.	1.0	9
66	Impedance-based interpretations in 2-dimensional electron gas conduction formed in the LaAlO 3 /Sr x Ca 1â^'x TiO 3 /SrTiO 3 system. Journal of Physics and Chemistry of Solids, 2016, 93, 131-136.	1.9	0
67	High quality interfacial sulfur passivation via H₂S pre-deposition annealing for an atomic-layer-deposited HfO₂ film on a Ge substrate. Journal of Materials Chemistry C, 2016, 4, 850-856.	2.7	16
68	Thickness-Dependent Electrocaloric Effect in Pb0.9La0.1Zr0.65Ti0.35O3 Films Grown by Solâ€“Gel Process. Journal of Electronic Materials, 2016, 45, 1057-1064.	1.0	12
69	Reliability of neuronal information conveyed by unreliable neuristor-based leaky integrate-and-fire neurons: a model study. Scientific Reports, 2015, 5, 9776.	1.6	38
70	Asymmetry in electrical properties of Alâ€doped TiO₂ film with respect to bias voltage. Physica Status Solidi - Rapid Research Letters, 2015, 9, 410-413.	1.2	10
71	Giant Electroresistive Ferroelectric Diode on 2DEG. Scientific Reports, 2015, 5, 10548.	1.6	10
72	Hardening of Biâ€“Te based alloys by dispersing B4C nanoparticles. Acta Materialia, 2015, 97, 68-74.	3.8	19

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73	Electric-field-induced Shift in the Threshold Voltage in LaAlO3/SrTiO3 Heterostructures. Scientific Reports, 2015, 5, 8023.	1.6	13
74	A differential method for measuring cooling performance of a thermoelectric module. Applied Thermal Engineering, 2015, 87, 209-213.	3.0	3
75	Sn doping in thermoelectric Bi2Te3 films by metal-organic chemical vapor deposition. Applied Surface Science, 2015, 353, 232-237.	3.1	18
76	Impedance-based interfacial analysis of the LaAlO3/SrTiO3 oxide heterostructure involving a 2-dimensional electron gas layer. Journal of Physics and Chemistry of Solids, 2015, 82, 60-66.	1.9	1
77	Thermoelectric Properties of Sn-Doped Bi0.4Sb1.6Te3 Thin Films. Journal of Electronic Materials, 2015, 44, 1573-1578.	1.0	3
78	Improved interface properties of atomic-layer-deposited HfO2 film on InP using interface sulfur passivation with H2S pre-deposition annealing. Applied Surface Science, 2015, 357, 2306-2312.	3.1	13
79	High mobility, large linear magnetoresistance, and quantum transport phenomena in Bi₂Te₃films grown by metallo-organic chemical vapor deposition (MOCVD). Nanoscale, 2015, 7, 17359-17365.	2.8	7
80	Growth Enhancement and Nitrogen Loss in ZnO_xN_y Low-Temperature Atomic Layer Deposition with NH₃. Journal of Physical Chemistry C, 2015, 119, 23470-23477.	1.5	7
81	Catalytic activity for oxygen reduction reaction on platinum-based coreâ€“shell nanoparticles: all-electron density functional theory. Nanoscale, 2015, 7, 15830-15839.	2.8	34
82	Control of the initial growth in atomic layer deposition of Pt films by surface pretreatment. Nanotechnology, 2015, 26, 304003.	1.3	21
83	Orientation-Controlled Growth of Pt Films on SrTiO₃ (001) by Atomic Layer Deposition. Chemistry of Materials, 2015, 27, 6779-6783.	3.2	9
84	Structure and Electrical Properties of Al-Doped HfO₂ and ZrO₂ Films Grown via Atomic Layer Deposition on Mo Electrodes. ACS Applied Materials & Interfaces, 2014, 6, 22474-22482.	4.0	63
85	Chemistry of active oxygen in RuO_x and its influence on the atomic layer deposition of TiO₂ films. Journal of Materials Chemistry C, 2014, 2, 9993-10001.	2.7	18
86	Multiprotocol-induced plasticity in artificial synapses. Nanoscale, 2014, 6, 15151-15160.	2.8	16
87	Fabrication and surface plasmon coupling studies on the dielectric/Ag structure for transparent conducting electrode applications. Optical Materials Express, 2014, 4, 2078.	1.6	16
88	Dynamic temperature response of electrocaloric multilayer capacitors. Applied Physics Letters, 2014, 104, .	1.5	11
89	Enhancement of Initial Growth of ZnO Films on Layer-Structured Bi₂Te₃ by Atomic Layer Deposition. Chemistry of Materials, 2014, 26, 6448-6453.	3.2	14
90	Evaluating the Top Electrode Material for Achieving an Equivalent Oxide Thickness Smaller than 0.4 nm from an Al-Doped TiO₂ Film. ACS Applied Materials & Interfaces, 2014, 6, 21632-21637.	4.0	31

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91	Thermopower Enhancement of Bi2Te3 Films by Doping I Ions. Journal of Electronic Materials, 2014, 43, 2000-2005.	1.0	9
92	Thermoelectric Properties of Highly Deformed and Subsequently Annealed p-Type (Bi0.25Sb0.75)2Te3 Alloys. Journal of Electronic Materials, 2014, 43, 1726-1732.	1.0	4
93	X-ray Irradiation Induced Reversible Resistance Change in Pt/TiO₂/Pt Cells. ACS Nano, 2014, 8, 1584-1589.	7.3	32
94	Growth of p-Type Tin(II) Monoxide Thin Films by Atomic Layer Deposition from Bis(1-dimethylamino-2-methyl-2propoxy)tin and H₂O. Chemistry of Materials, 2014, 26, 6088-6091.	3.2	76
95	Giant electrode effect on tunnelling electroresistance in ferroelectric tunnel junctions. Nature Communications, 2014, 5, 5414.	5.8	123
96	Strain-assisted, low-temperature synthesis of high-performance thermoelectric materials. Physical Chemistry Chemical Physics, 2014, 16, 3529.	1.3	13
97	Controlling the Al-Doping Profile and Accompanying Electrical Properties of Rutile-Phased TiO₂ Thin Films. ACS Applied Materials & Interfaces, 2014, 6, 7910-7917.	4.0	21
98	Nonvolatile Resistance Switching on Two-Dimensional Electron Gas. ACS Applied Materials & Interfaces, 2014, 6, 17785-17791.	4.0	5
99	Impact of parasitic thermal effects on thermoelectric property measurements by Harman method. Review of Scientific Instruments, 2014, 85, 045108.	0.6	21
100	SnO 2 thin films grown by atomic layer deposition using a novel Sn precursor. Applied Surface Science, 2014, 320, 188-194.	3.1	35
101	Atomic layer deposition of HfO2 thin films using H2O2 as oxidant. Applied Surface Science, 2014, 301, 451-455.	3.1	24
102	Chemical structures and electrical properties of atomic layer deposited HfO2 thin films grown at an extremely low temperature (â‰100Â°C) using O3 as an oxygen source. Applied Surface Science, 2014, 292, 852-856.	3.1	32
103	Oxygen-Vacancy-Induced Polar Behavior in (LaFeO3)2/(SrFeO3) Superlattices. Nano Letters, 2014, 14, 2694-2701.	4.5	53
104	Mass-Production Memories (DRAM and Flash). , 2014, , 73-122.		8
105	Nonâ€Volatile Control of 2DEG Conductivity at Oxide Interfaces. Advanced Materials, 2013, 25, 4612-4617.	11.1	47
106	Influences of metal, non-metal precursors, and substrates on atomic layer deposition processes for the growth of selected functional electronic materials. Coordination Chemistry Reviews, 2013, 257, 3154-3176.	9.5	48
107	Control of conducting filaments in TiO2 films by a thin interfacial conducting oxide layer at the cathode. Applied Physics Letters, 2013, 102, 082903.	1.5	7
108	Titanium dioxide thin films for next-generation memory devices. Journal of Materials Research, 2013, 28, 313-325.	1.2	67

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109	Atomic Layer Deposition of SrTiO₃ Films with Cyclopentadienyl-Based Precursors for Metalâ€“Insulatorâ€“Metal Capacitors. Chemistry of Materials, 2013, 25, 953-961.	3.2	69
110	Modular instrument mounting system for variable environment in operando X-ray experiments. Review of Scientific Instruments, 2013, 84, 025111.	0.6	10
111	Capacitanceâ€“voltage analysis of LaAlO3/SrTiO3 heterostructures. Applied Physics Letters, 2013, 102, 112906.	1.5	8
112	Effect of Mechanical Deformation on Thermoelectric Properties of p-Type(Bi0.225Sb0.775)2Te3Alloys. Journal of Nanomaterials, 2013, 2013, 1-6.	1.5	3
113	In situ x-ray studies of oxygen surface exchange behavior in thin film La_{0.6}Sr_{0.4}Co_{0.2}Fe_{0.8}O_{3â˜Î´}. Applied Physics Letters, 2012, 101, 051603.	1.5	20
114	Study on Initial Growth Behavior of RuO₂ Film Grown by Pulsed Chemical Vapor Deposition: Effects of Substrate and Reactant Feeding Time. Chemistry of Materials, 2012, 24, 1407-1414.	3.2	23
115	Impact of Bimetal Electrodes on Dielectric Properties of TiO₂ and Al-Doped TiO₂ Films. ACS Applied Materials & Interfaces, 2012, 4, 4726-4730.	4.0	18
116	Atomic layer deposited HfO2 and HfO2/TiO2 bi-layer films using a heteroleptic Hf-precursor for logic and memory applications. Journal of Materials Chemistry, 2011, 21, 18497.	6.7	12
117	Improvement in the leakage current characteristic of metal-insulator-metal capacitor by adopting RuO2 film as bottom electrode. Applied Physics Letters, 2011, 99, .	1.5	58
118	Role of Interfacial Reaction in Atomic Layer Deposition of TiO₂ Thin Films Using Ti(O-iPr)₂(tmhd)₂ on Ru or RuO₂ Substrates. Chemistry of Materials, 2011, 23, 976-983.	3.2	26
119	Electrically Benign Ru Wet Etching Method for Fabricating Ruâ•TiO[sub 2]â•Ru Capacitor. Journal of the Electrochemical Society, 2011, 158, G47.	1.3	2
120	Atomic Layer Deposition of SrTiO₃ Thin Films with Highly Enhanced Growth Rate for Ultrahigh Density Capacitors. Chemistry of Materials, 2011, 23, 2227-2236.	3.2	112
121	Relation Between Enhancement in Growth and Thickness-Dependent Crystallization in ALD TiO[sub 2] Thin Films. Journal of the Electrochemical Society, 2011, 158, D6.	1.3	44
122	Atomic layer deposition of TiO₂ and Alâ€doped TiO₂ films on Ir substrates for ultralow leakage currents. Physica Status Solidi - Rapid Research Letters, 2011, 5, 262-264.	1.2	9
123	Effect of crystalline structure of TiO2 substrates on initial growth of atomic layer deposited Ru thin films. Applied Surface Science, 2011, 257, 4302-4305.	3.1	13
124	The mechanism for the suppression of leakage current in high dielectric TiO2 thin films by adopting ultra-thin HfO2 films for memory application. Journal of Applied Physics, 2011, 110, 024105.	1.1	26
125	High Growth Rate in Atomic Layer Deposition of TiO2 thin films by UV Irradiation. Electrochemical and Solid-State Letters, 2011, 14, H146.	2.2	14
126	Local Epitaxial Growth of Ru Thin Films by Atomic Layer Deposition at Low Temperature. Journal of the Electrochemical Society, 2011, 158, D477.	1.3	17

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127	Capacitors with an Equivalent Oxide Thickness of <0.5 nm for Nanoscale Electronic Semiconductor Memory. Advanced Functional Materials, 2010, 20, 2989-3003.	7.8	189
128	Growth of RuO₂ Thin Films by Pulsed-Chemical Vapor Deposition Using RuO₄ Precursor and 5% H₂ Reduction Gas. Chemistry of Materials, 2010, 22, 5700-5706.	3.2	40
129	Role of Ru nano-dots embedded in TiO2 thin films for improving the resistive switching behavior. Applied Physics Letters, 2010, 97, .	1.5	49
130	Permittivity Enhanced Atomic Layer Deposited HfO₂ Thin Films Manipulated by a Rutile TiO₂ Interlayer. Chemistry of Materials, 2010, 22, 4419-4425.	3.2	29
131	Investigation on the Growth Initiation of Ru Thin Films by Atomic Layer Deposition. Chemistry of Materials, 2010, 22, 2850-2856.	3.2	74
132	Growth and Characterization of Conducting ZnO Thin Films by Atomic Layer Deposition. Bulletin of the Korean Chemical Society, 2010, 31, 2503-2508.	1.0	64
133	Atomic Layer Deposition of TiO[sub 2] Films on Ru Buffered TiN Electrode for Capacitor Applications. Journal of the Electrochemical Society, 2009, 156, G71.	1.3	33
134	Liquid Injection Atomic Layer Deposition of Crystalline TiO[sub 2] Thin Films with a Smooth Morphology from Ti(O-i-Pr)[sub 2](DPM)[sub 2]. Journal of the Electrochemical Society, 2009, 156, D296.	1.3	23
135	Plasma-Enhanced Atomic Layer Deposition of TiO[sub 2] and Al-Doped TiO[sub 2] Films Using N[sub 2]O and O[sub 2] Reactants. Journal of the Electrochemical Society, 2009, 156, G138.	1.3	46
136	Growth of Noble Metal Ru Thin Films by Liquid Injection Atomic Layer Deposition. Journal of Physical Chemistry C, 2009, 113, 11329-11335.	1.5	26
137	Alâ€Doped TiO₂ Films with Ultralow Leakage Currents for Next Generation DRAM Capacitors. Advanced Materials, 2008, 20, 1429-1435.	11.1	281
138	Novel postâ€process for the passivation of a CMOS biosensor. Physica Status Solidi - Rapid Research Letters, 2008, 2, 4-6.	1.2	27
139	Atomic layer deposition of hafnium oxide from tert-butoxytris(ethylmethylamido)hafnium and ozone: rapid growth, high density and thermal stability. Journal of Materials Chemistry, 2008, 18, 4324.	6.7	43
140	Controlling the Composition of Doped Materials by ALD: A Case Study for Al-Doped TiO[sub 2] Films. Electrochemical and Solid-State Letters, 2008, 11, G27.	2.2	15
141	Growth Behavior of Al-Doped TiO₂ Thin Films by Atomic Layer Deposition. Chemistry of Materials, 2008, 20, 3723-3727.	3.2	69
142	Atomic Layer Deposition of ZrO2 Thin Films with High Dielectric Constant on TiN Substrates. Electrochemical and Solid-State Letters, 2008, 11, G9.	2.2	65
143	Atomic Layer Deposition of Ru Thin Films Using 2,4-(Dimethylpentadienyl)(ethylcyclopentadienyl)Ru by a Liquid Injection System. Journal of the Electrochemical Society, 2007, 154, D95.	1.3	88
144	Characteristics of a Capacitive Probe Array for Direct Surface Charge Detection. Electrochemical and Solid-State Letters, 2007, 10, H34.	2.2	0

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145	Atomic Layer Deposition of Ru Thin Films Using 2,4-(dimethylpentadienyl)(ethylcyclopentadienyl) Ru by a Liquid Injection System. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
146	Impact of O3 feeding time on TiO2 films grown by atomic layer deposition for memory capacitor applications. Journal of Applied Physics, 2007, 102, 024109.	1.1	46
147	First-principles study of point defects in rutileTiO2â^'x. Physical Review B, 2006, 73, .	1.1	205
148	Transformation of the Crystalline Structure of an ALD TiO[sub 2] Film on a Ru Electrode by O[sub 3] Pretreatment. Electrochemical and Solid-State Letters, 2006, 9, F5.	2.2	66
149	Influence of the oxygen concentration of atomic-layer-deposited HfO2 gate dielectric films on the electron mobility of polycrystalline-Si gate transistors. Journal of Applied Physics, 2006, 99, 094501.	1.1	23
150	Low Temperature (<100Â°C) Deposition of Aluminum Oxide Thin Films by ALD with O[sub 3] as Oxidant. Journal of the Electrochemical Society, 2006, 153, F69.	1.3	144
151	Comparison between ZnO films grown by atomic layer deposition using H2O or O3 as oxidant. Thin Solid Films, 2005, 478, 103-108.	0.8	136
152	Electrical properties of high-k HfO2 films on Si1â^'xGex substrates. Microelectronic Engineering, 2005, 80, 222-225.	1.1	11
153	Influence of the oxygen concentration of atomic-layer-deposited HfO2 films on the dielectric property and interface trap density. Applied Physics Letters, 2005, 86, 112907.	1.5	50
154	Structurally and Electrically Uniform Deposition of High-k TiO[sub 2] Thin Films on a Ru Electrode in Three-Dimensional Contact Holes Using Atomic Layer Deposition. Electrochemical and Solid-State Letters, 2005, 8, F59.	2.2	35
155	Chemically Conformal ALD of SrTiO[sub 3] Thin Films Using Conventional Metallorganic Precursors. Journal of the Electrochemical Society, 2005, 152, C229.	1.3	66
156	Growth Characteristics of Atomic Layer Deposited TiO[sub 2] Thin Films on Ru and Si Electrodes for Memory Capacitor Applications. Journal of the Electrochemical Society, 2005, 152, C552.	1.3	64
157	Fabrication of a metal-oxide-semiconductor-type capacitive microtip array using SiO2 or HfO2 gate insulators. Applied Physics Letters, 2004, 85, 5412-5414.	1.5	1
158	Atomic-layer-deposited Al2O3 thin films with thin SiO2 layers grown by in situ O3 oxidation. Journal of Applied Physics, 2004, 96, 2323-2329.	1.1	68
159	High dielectric constant TiO2 thin films on a Ru electrode grown at 250â€‰Â°C by atomic-layer deposition. Applied Physics Letters, 2004, 85, 4112-4114.	1.5	305